

SGH40N60UF

Ultra-Fast IGBT

General Description

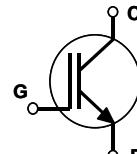
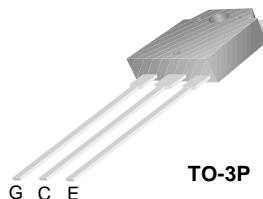
Fairchild's UF series of Insulated Gate Bipolar Transistors (IGBTs) provides low conduction and switching losses. The UF series is designed for applications such as motor control and general inverters where high speed switching is a required feature.

Features

- High speed switching
- Low saturation voltage : $V_{CE(sat)} = 2.1$ V @ $I_C = 20$ A
- High input impedance

Applications

AC & DC motor controls, general purpose inverters, robotics, and servo controls.



Absolute Maximum Ratings

$T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Description	SGH40N60UF	Units
V_{CES}	Collector-Emitter Voltage	600	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current @ $T_C = 25^\circ\text{C}$	40	A
	Collector Current @ $T_C = 100^\circ\text{C}$	20	A
$I_{CM(1)}$	Pulsed Collector Current	160	A
P_D	Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$	160	W
	Maximum Power Dissipation @ $T_C = 100^\circ\text{C}$	64	W
T_J	Operating Junction Temperature	-55 to +150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temp. for Soldering Purposes, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

Notes :

(1) Repetitive rating : Pulse width limited by max. junction temperature

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	--	0.77	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	40	$^\circ\text{C}/\text{W}$

Electrical Characteristics of the IGBT

$T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
BV_{CES}	Collector-Emitter Breakdown Voltage	$V_{GE} = 0\text{V}$, $I_C = 250\text{uA}$	600	--	--	V
$\Delta B_{V_{CES}}/\Delta T_J$	Temperature Coefficient of Breakdown Voltage	$V_{GE} = 0\text{V}$, $I_C = 1\text{mA}$	--	0.6	--	$\text{V}/^\circ\text{C}$
I_{CES}	Collector Cut-Off Current	$V_{CE} = V_{CES}$, $V_{GE} = 0\text{V}$	--	--	250	uA
I_{GES}	G-E Leakage Current	$V_{GE} = V_{GES}$, $V_{CE} = 0\text{V}$	--	--	± 100	nA
On Characteristics						
$V_{GE(\text{th})}$	G-E Threshold Voltage	$I_C = 20\text{mA}$, $V_{CE} = V_{GE}$	3.5	4.5	6.5	V
$V_{CE(\text{sat})}$	Collector to Emitter Saturation Voltage	$I_C = 20\text{A}$, $V_{GE} = 15\text{V}$	--	2.1	2.6	V
		$I_C = 40\text{A}$, $V_{GE} = 15\text{V}$	--	2.6	--	V
Dynamic Characteristics						
C_{ies}	Input Capacitance	$V_{CE} = 30\text{V}$, $V_{GE} = 0\text{V}$, $f = 1\text{MHz}$	--	1430	--	pF
C_{oes}	Output Capacitance		--	170	--	pF
C_{res}	Reverse Transfer Capacitance		--	50	--	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 300\text{ V}$, $I_C = 20\text{A}$, $R_G = 10\Omega$, $V_{GE} = 15\text{V}$, Inductive Load, $T_C = 25^\circ\text{C}$	--	15	--	ns
t_r	Rise Time		--	30	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	65	130	ns
t_f	Fall Time		--	50	150	ns
E_{on}	Turn-On Switching Loss		--	160	--	uJ
E_{off}	Turn-Off Switching Loss		--	200	--	uJ
E_{ts}	Total Switching Loss		--	360	600	uJ
$t_{d(on)}$	Turn-On Delay Time		--	30	--	ns
t_r	Rise Time	$V_{CC} = 300\text{ V}$, $I_C = 20\text{A}$, $R_G = 10\Omega$, $V_{GE} = 15\text{V}$, Inductive Load, $T_C = 125^\circ\text{C}$	--	37	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	110	200	ns
t_f	Fall Time		--	144	250	ns
E_{on}	Turn-On Switching Loss		--	310	--	uJ
E_{off}	Turn-Off Switching Loss		--	430	--	uJ
E_{ts}	Total Switching Loss		--	740	1200	uJ
Q_g	Total Gate Charge	$V_{CE} = 300\text{ V}$, $I_C = 20\text{A}$, $V_{GE} = 15\text{V}$	--	97	150	nC
Q_{ge}	Gate-Emitter Charge		--	20	30	nC
Q_{gc}	Gate-Collector Charge		--	25	40	nC
L_e	Internal Emitter Inductance	Measured 5mm from PKG	--	14	--	nH

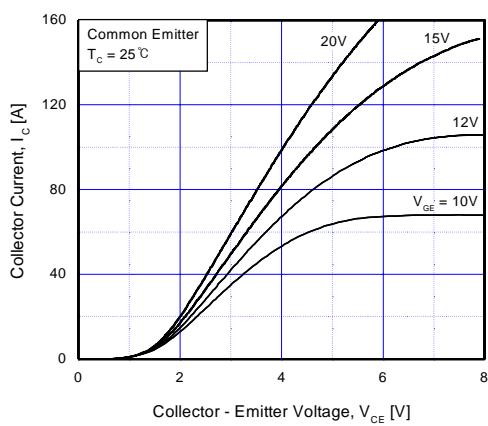


Fig 1. Typical Output Characteristics

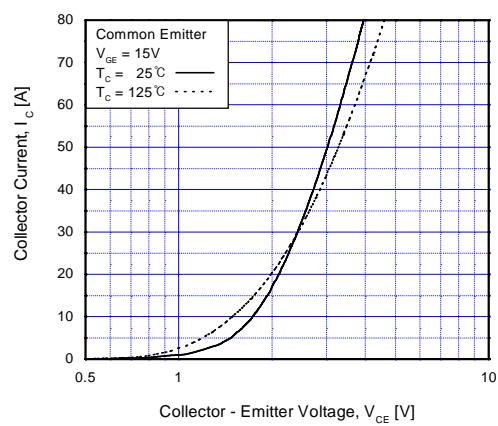


Fig 2. Typical Saturation Voltage Characteristics

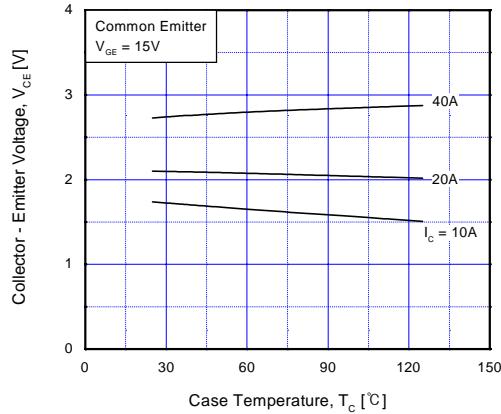


Fig 3. Saturation Voltage vs. Case Temperature at Variant Current Level

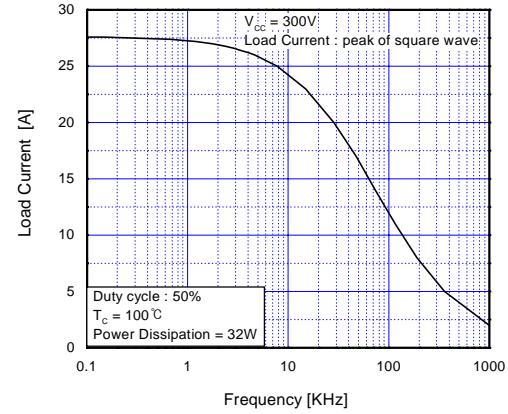
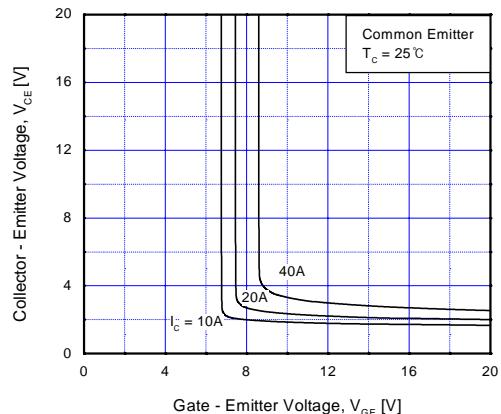
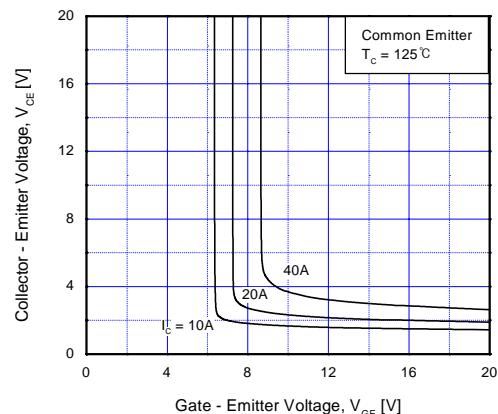


Fig 4. Load Current vs. Frequency

Fig 5. Saturation Voltage vs. V_{GE}Fig 6. Saturation Voltage vs. V_{GE}

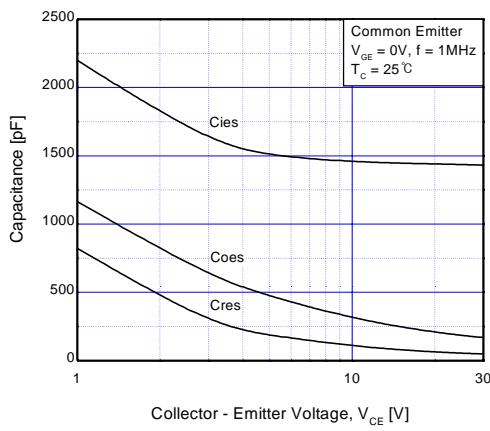


Fig 7. Capacitance Characteristics

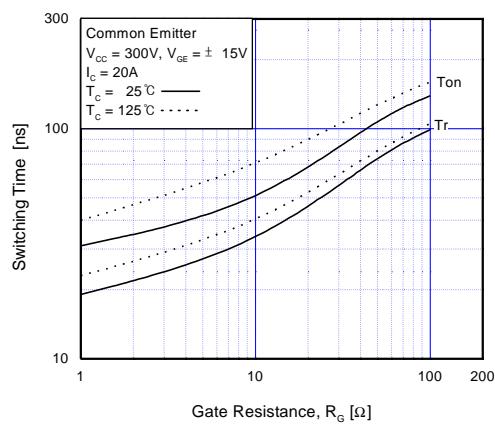


Fig 8. Turn-On Characteristics vs. Gate Resistance

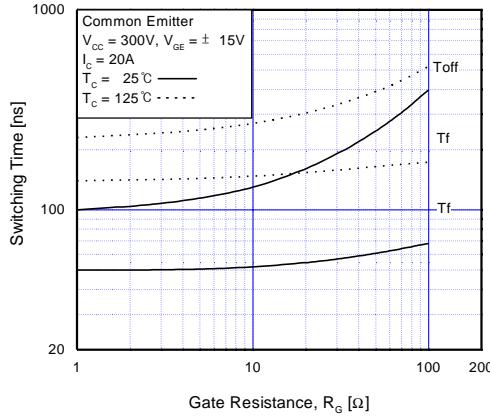


Fig 9. Turn-Off Characteristics vs. Gate Resistance

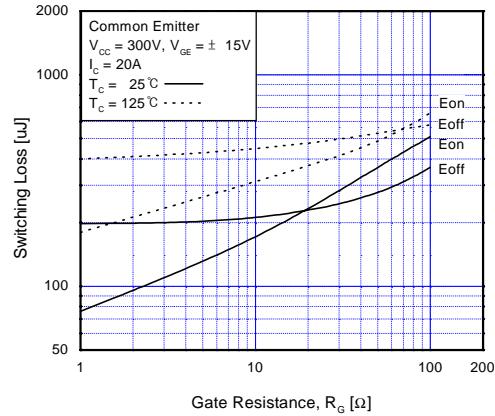


Fig 10. Switching Loss vs. Gate Resistance

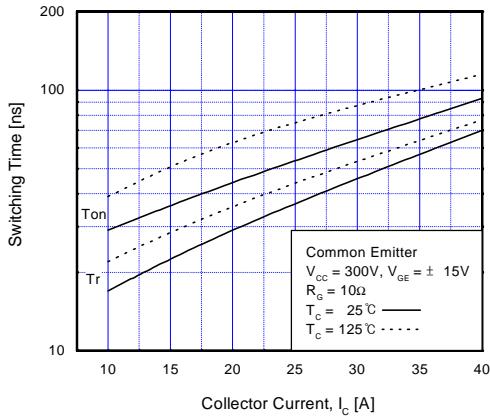


Fig 11. Turn-On Characteristics vs. Collector Current

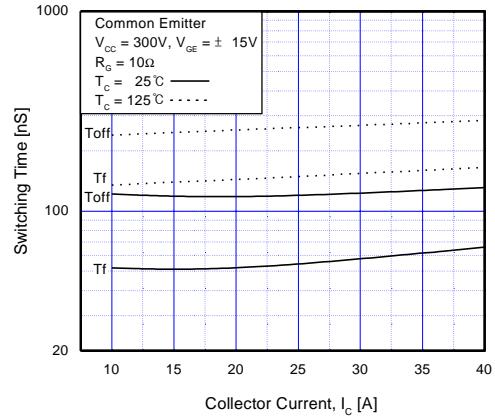


Fig 12. Turn-Off Characteristics vs. Collector Current

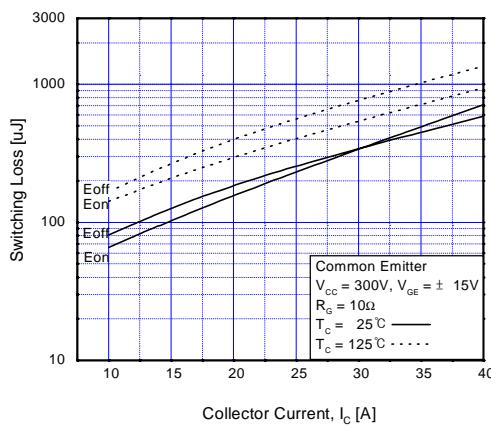


Fig 13. Switching Loss vs. Collector Current

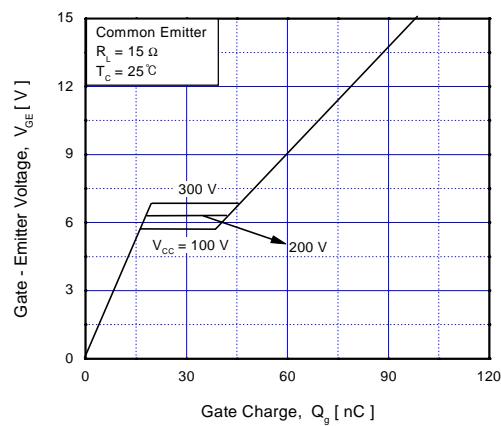


Fig 14. Gate Charge Characteristics

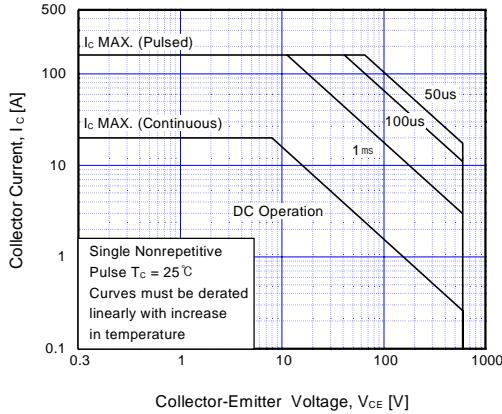


Fig 15. SOA Characteristics

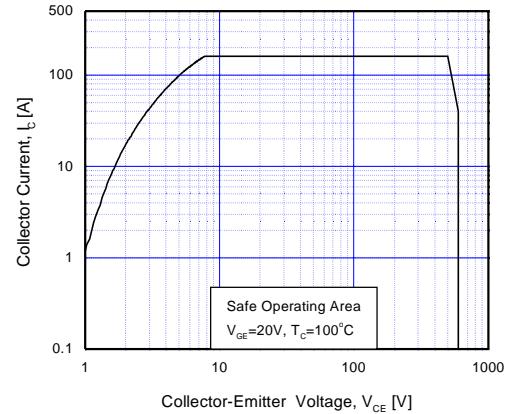


Fig 16. Turn-Off SOA Characteristics

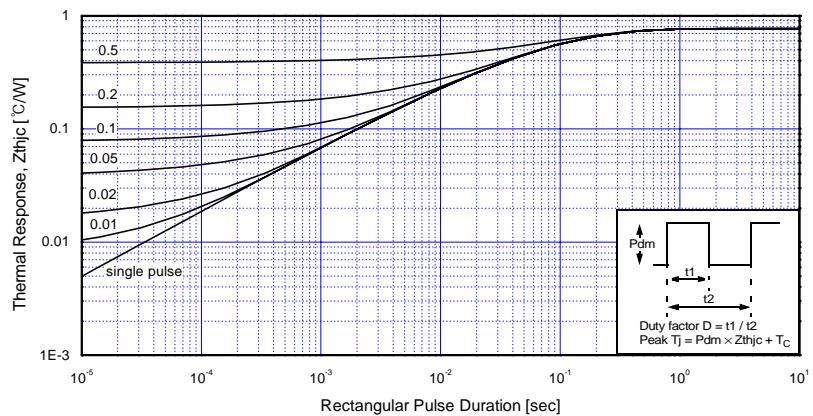
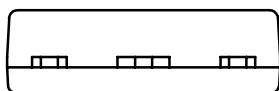
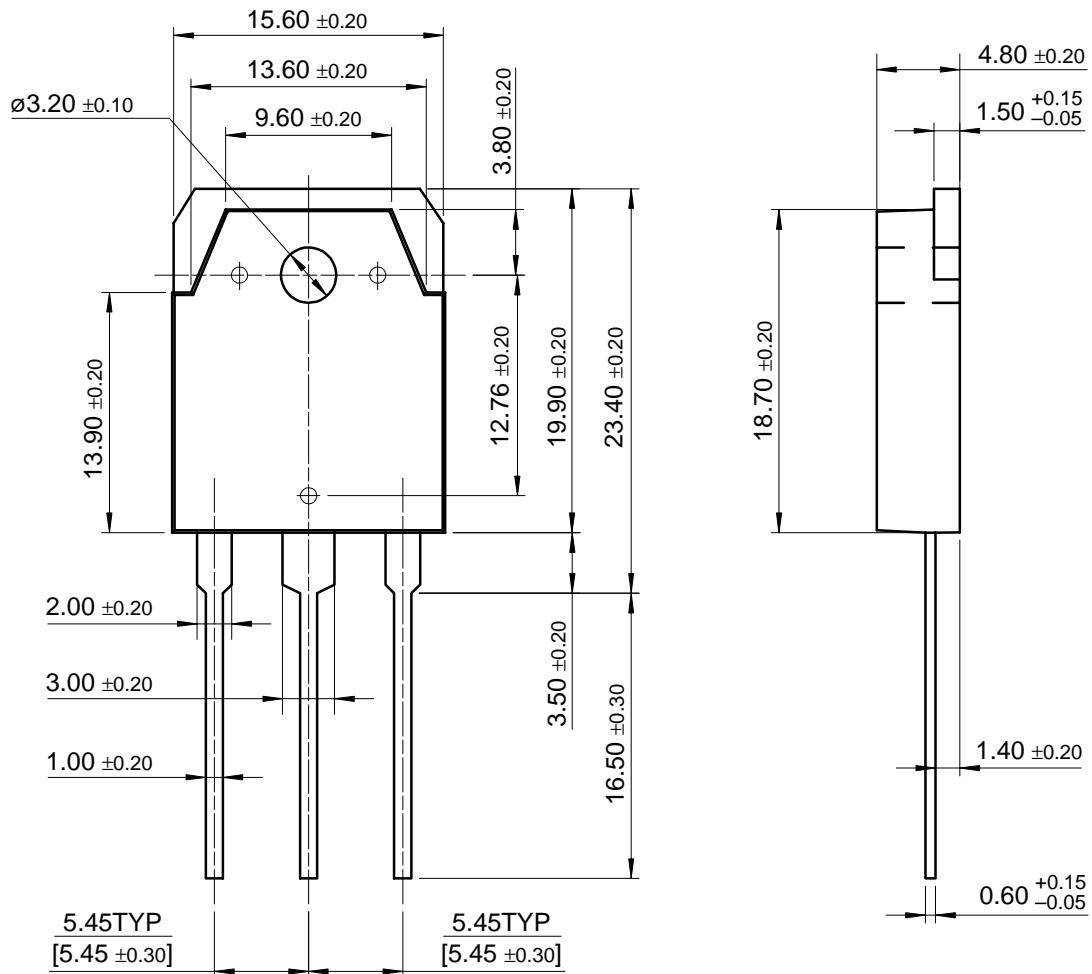


Fig 17. Transient Thermal Impedance of IGBT

SGH40N60UF

Package Dimension

TO-3P



Dimensions in Millimeters

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